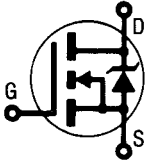


INTERNATIONAL RECTIFIER

AVALANCHE ENERGY RATED AND dv/dt RATEDHEXFET[®] TRANSISTOR

IRFI064



N-CHANNEL

60 Volt, 0.017 Ohm HEXFET

The HEXFET[®] technology is the key to International Rectifier's advanced line of power MOSFET transistors. The efficient geometry design achieves very low on-state resistance combined with high transconductance.

The HEXFET transistors also feature all of the well established advantages of MOSFETs such as voltage control, very fast switching, ease of paralleling and temperature stability of the electrical parameters.

They are well suited for applications such as switching power supplies and virtually any application where military and/or high reliability is required.

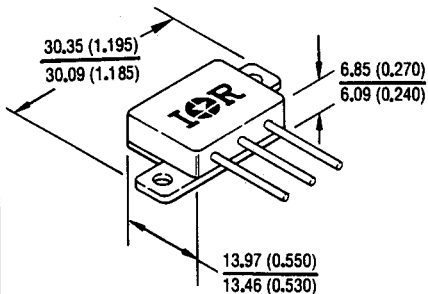
Product Summary

Part Number	BV_{DSS}	$R_{DS(on)}$	I_D
IRFI064	60V	0.017 Ω	45A*

FEATURES:

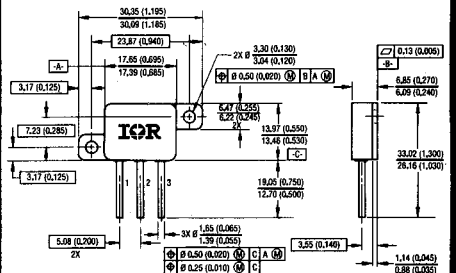
- Avalanche Energy Rating
- Isolated and Hermetically Sealed
- Alternative to TO-3 Package
- Simple Drive Requirements
- Ease of Paralleling
- Ceramic Eyelets

CASE STYLE AND DIMENSIONS



CAUTION

BERYLLIA WARNING PER MIL-S-19500
SEE PAGE I-251



NOTES:

- 1 DIMENSIONING & TOLERANCING PER ANSI Y14.5M - 1982.
- 2 DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).

LEGEND

- 1 DRAIN
- 2 SOURCE
- 3 GATE

*For optional leadforms see page I-251, fig. 15

Conforms to JEDEC Outline TO-259AA*
Dimensions in Millimeters and (Inches)

Absolute Maximum Ratings

Parameter	IRFI064	Units
I_D @ $V_{GS} = 10V$, $T_C = 25^\circ C$ Continuous Drain Current	45*	A
I_D @ $V_{GS} = 10V$, $T_C = 100^\circ C$ Continuous Drain Current	45*	
I_{DM} Pulsed Drain Current ①	400	
P_D @ $T_C = 25^\circ C$ Max. Power Dissipation	300	W
Linear Derating Factor	2.4	W/K ⑤
V_{GS} Gate-to-Source Voltage	± 20	V
EAS Single Pulse Avalanche Energy ②	620	mJ
dv/dt Peak Diode Recovery dv/dt ③	4.5	V/ns
T_J Operating Junction	-55 to 150	$^\circ C$
T_{STG} Storage Temperature Range		
Lead Temperature	300 (0.063 in. (1.6 mm) from case for 10s)	
Weight	10.9 (typical)	g

* I_D current limited by pin diameterElectrical Characteristics @ $T_J = 25^\circ C$ (Unless Otherwise Specified)

Parameter	Min.	Typ.	Max.	Units	Test Conditions	
BV_{DSS} Drain-to-Source Breakdown Voltage	60	—	—	V	$V_{GS} = 0V$, $I_D = 1.0$ mA	
$\Delta BV_{DSS}/\Delta T_J$ Temperature Coefficient of Breakdown Voltage	—	0.048	—	V/°C	Reference to 25°C, $I_D = 1.0$ mA	
$R_{DS(on)}$ Static Drain-to-Source On-State Resistance	—	—	0.017	Ω	$V_{GS} = 10V$, $I_D = 45A$ ④	
$V_{GS(th)}$ Gate Threshold Voltage	2.0	—	4.0	V	$V_{DS} = V_{GS}$, $I_D = 250$ μA	
g_{fs} Forward Transconductance	21	—	—	S (tt)	$V_{DS} \geq 15V$, $I_{DS} = 45A$ ④	
I_{DSS} Zero Gate Voltage Drain Current	—	—	25	μA	$V_{DS} = 0.8 \times \text{Max. Rating}$, $V_{GS} = 0V$	
	—	—	250		$V_{DS} = 0.8 \times \text{Max. Rating}$ $V_{GS} = 0V$, $T_J = 125^\circ C$	
I_{GSS} Gate-to-Source Leakage Forward	—	—	100	nA	$V_{GS} = 20V$	
I_{GSS} Gate-to-Source Leakage Reverse	—	—	-100		$V_{GS} = -20V$	
Q_g Total Gate Charge	—	—	240	nC	$V_{GS} = 10V$, $I_D = 45A$	
Q_{gs} Gate-to-Source Charge	—	—	53		$V_{DS} = 0.5 \times \text{Max. Rating}$	
Q_{gd} Gate-to-Drain ("Miller") Charge	—	—	78		See Fig. 6 and 14	
$t_{d(on)}$ Turn-On Delay Time	—	—	27	ns	$V_{DD} = 30V$, $I_D = 45A$, $R_G = 2.35\Omega$	
t_r Rise Time	—	—	120		See Fig. 11	
$t_{d(off)}$ Turn-Off Delay Time	—	—	76			
t_f Fall Time	—	—	93			
L_D Internal Drain Inductance	—	5.0	—	nH	Measured from the drain lead, 6 mm (0.25 in.) from package to center of die.	Modified MOSFET symbol showing the internal inductances. 
L_S Internal Source Inductance	—	13	—		Measured from the source lead, 6 mm (0.25 in.) from package to source bonding pad.	
C_{iss} Input Capacitance	—	7400	—	pF	$V_{GS} = 0V$, $V_{DS} = 25V$	
C_{oss} Output Capacitance	—	3200	—		$f = 1.0$ MHz	
C_{rss} Reverse Transfer Capacitance	—	540	—		See Fig. 5	
C_{DC} Drain-to-Case Capacitance	—	12	—		$f = 1.0$ MHz	

Source-Drain Diode Ratings and Characteristics

Parameter	Min.	Typ.	Max.	Units	Test Conditions
I_S Continuous Source Current (Body Diode)	—	—	45*	A	Modified MOSFET symbol showing the integral Reverse p-n junction rectifier. 
I_{SM} Pulsed Source Current (Body Diode) ①	—	—	400		
V_{SD} Diode Forward Voltage	—	—	3.0	V	$T_J = 25^\circ\text{C}$, $I_S = 45\text{A}$, $V_{GS} = 0\text{V}$ ④
t_{rr} Reverse Recovery Time	—	—	220	nS	$T_J = 25^\circ\text{C}$, $I_F = 45\text{A}$, $di/dt = \leq 100\text{ A}/\mu\text{s}$ ④
Q_{RR} Reverse Recovery Charge	—	—	1.1	μC	$V_{DD} \leq 50\text{V}$
t_{on} Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by $L_S + L_D$.				

* I_S current limited by pin diameter

Thermal Resistance

Parameter	Min.	Typ.	Max.	Units	Test Conditions
R_{thJC} Junction-to-Case	—	—	0.42	K/W ⑤	
R_{thCS} Case-to-Sink	—	0.21	—		Mounting surface flat, smooth, and greased
R_{thJA} Junction-to-Ambient	—	—	30		Typical socket mount

① Repetitive Rating; Pulse width limited by maximum junction temperature (see figure 9)
Refer to current HEXFET reliability report

② @ $V_{DD} = 25\text{V}$, Starting $T_J = 25^\circ\text{C}$,
 $L \geq 79\text{ mH}$, $R_G = 25\Omega$,
Peak $I_L = 45\text{A}$

③ $I_{SD} \leq 130\text{A}$, $di/dt \leq 300\text{ A}/\mu\text{s}$,
 $V_{DD} \leq BV_{DSS}$, $T_J \leq 125^\circ\text{C}$
Suggested $R_G = 2.35\Omega$

④ Pulse width $\leq 300\text{ }\mu\text{s}$; Duty Cycle $\leq 2\%$

⑤ $K/W = ^\circ\text{C}/W$
 $W/K = W/^\circ\text{C}$

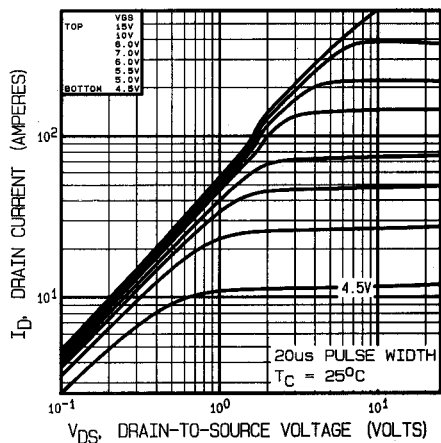
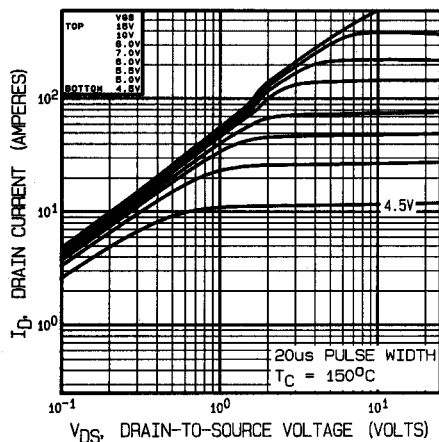
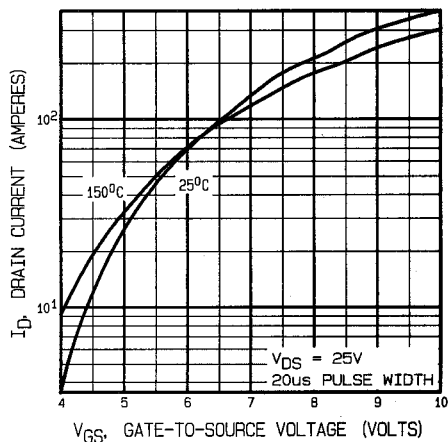
Fig. 1 — Typical Output Characteristics, $T_C = 25^\circ\text{C}$ Fig. 2 — Typical Output Characteristics, $T_C = 150^\circ\text{C}$ 

Fig. 3 — Typical Transfer Characteristics

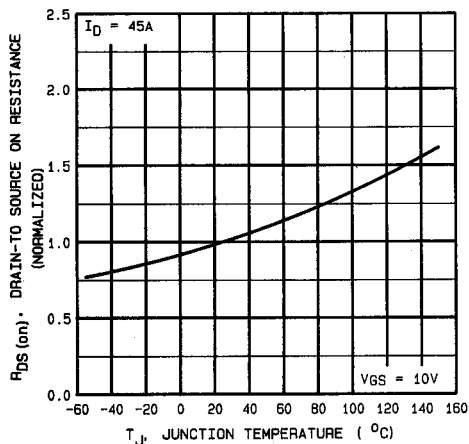


Fig. 4 — Normalized On-Resistance Vs. Temperature

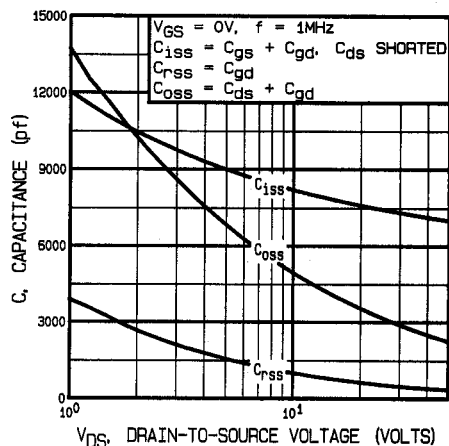


Fig. 5 — Typical Capacitance Vs. Drain-to-Source Voltage

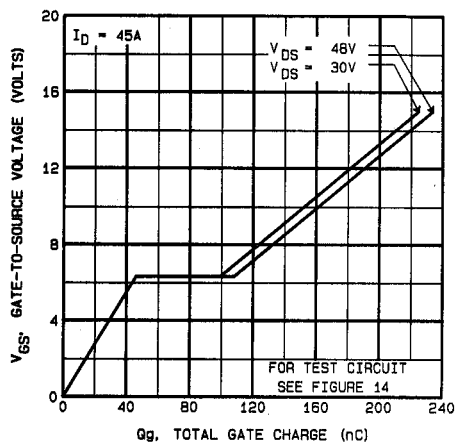


Fig. 6 — Typical Gate Charge Vs. Gate-to-Source Voltage

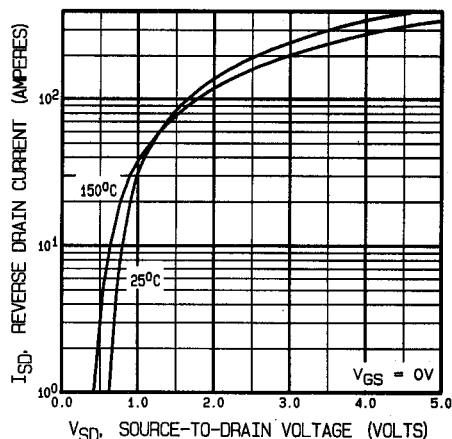


Fig. 7 — Typical Source-Drain Diode Forward Voltage

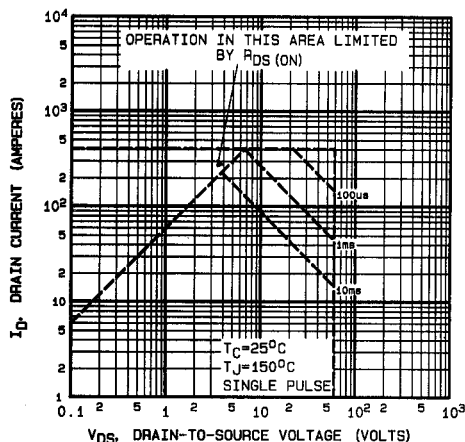


Fig. 8 — Maximum Safe Operating Area

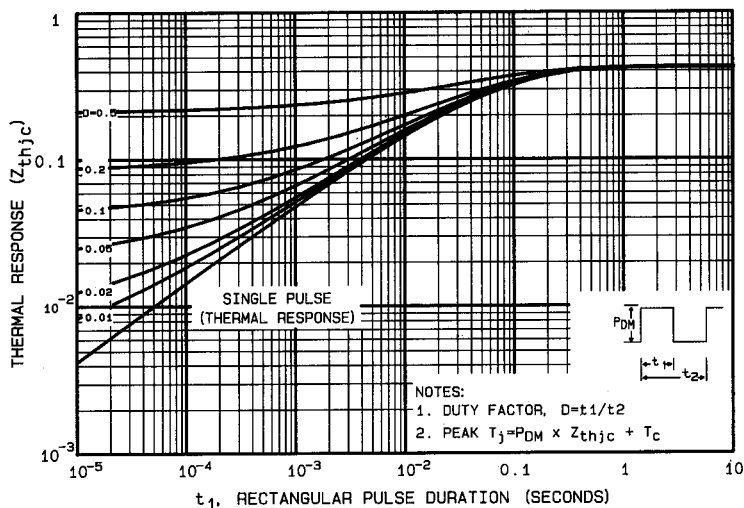


Fig. 9 — Maximum Effective Transient Thermal Impedance, Junction-to-Case Vs. Pulse Duration

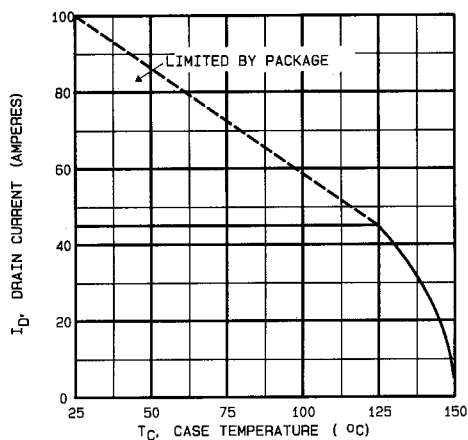


Fig. 10 — Maximum Drain Current Vs. Case Temperature

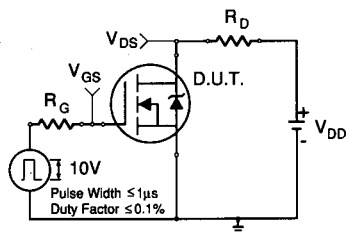


Fig. 11a — Switching Time Test Circuit

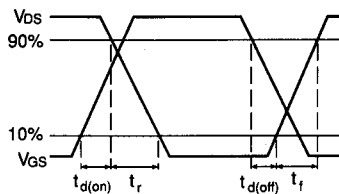


Fig. 11b — Switching Time Waveforms

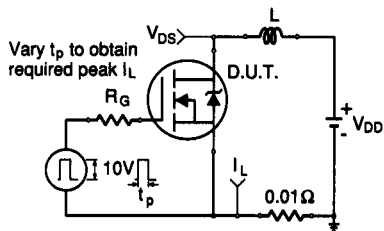


Fig. 12a — Unclamped Inductive Test Circuit

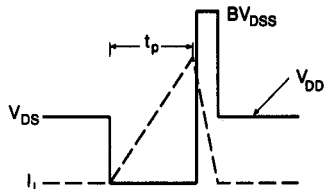


Fig. 12b — Unclamped Inductive Waveforms

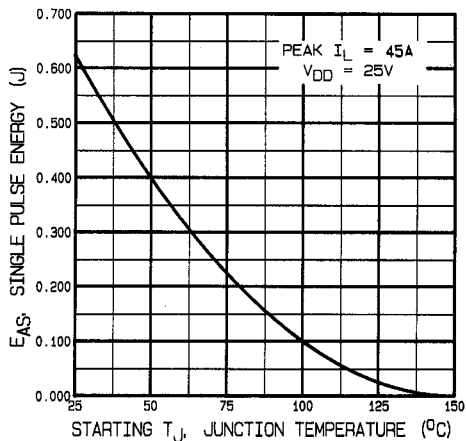
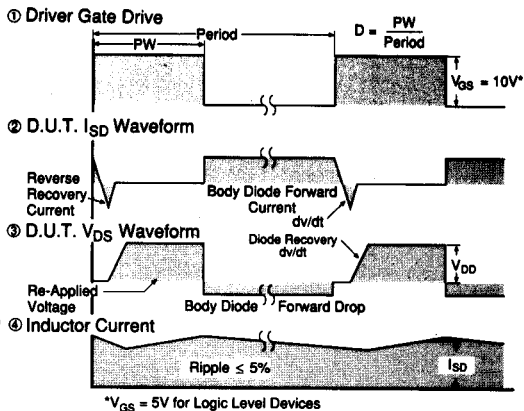
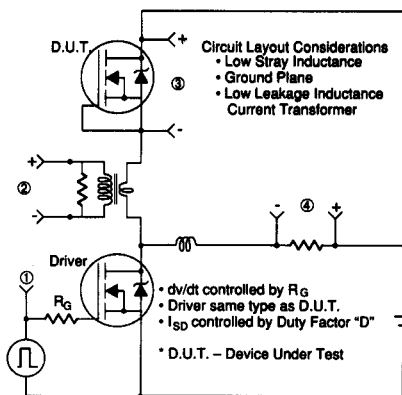


Fig. 12c — Maximum Avalanche Energy Vs. Starting Junction Temperature


 Fig. 13 — Peak Diode Recovery dv/dt Test Circuit

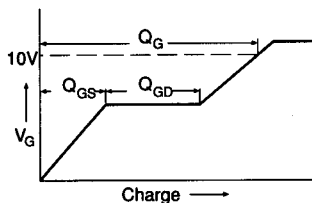


Fig. 14a — Basic Gate Charge Waveform

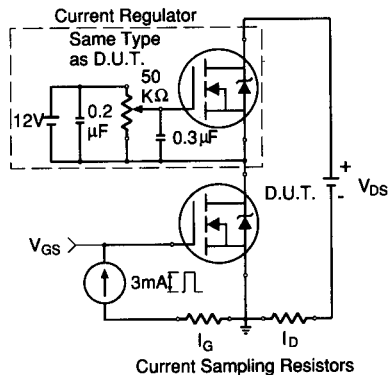


Fig. 14b — Gate Charge Test Circuit

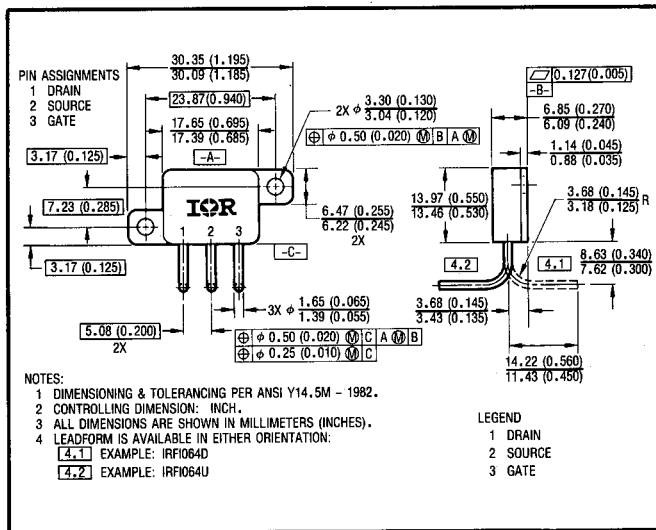


Fig. 15 — Optional Leadforms for Outline TO-259

BERYLLIA WARNING PER MIL-S-19500

Packages containing beryllia shall not be ground, sandblasted, machined, or have other operations performed on them which will produce beryllia or beryllium dust. Furthermore, beryllium oxide packages shall not be placed in acids that will produce fumes containing beryllium.